

METHOD OF MEASURING CRYSTAL DEFECTS IN THIN Si/SiGe BILAYERS  
ABSTRACT OF THE DISCLOSURE

Described herein is a method for delineating crystalline defects in a thin Si layer over a SiGe alloy layer. The method uses a defect etchant with a high-defect selectivity in Si. The Si is etched down to a thickness that allows the defect pits to reach the underlying SiGe layer. A second etchant, which can be the same or different from the defect etchant, is then used which attacks the SiGe layer under the pits while leaving Si intact.